

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

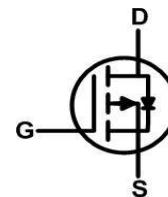
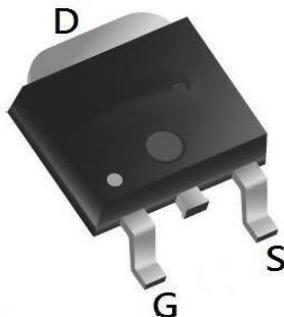
Product Summary


BVDSS	RDS(ON)	ID
-30V	2.5mΩ	-120A

Description

The XXW12P03D is the high cell density trenched P-ch MOSFETs, which provide excellent RDS(ON) and gate charge for most of the synchronous buck converter applications.

The XXW12P03D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	-120	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	-80	A
I _{DM}	Pulsed Drain Current ²	-470	A
EAS	Single Pulse Avalanche Energy ³	580	mJ
I _{AS}	Avalanche Current	-80	A
P _D @T _C =25°C	Total Power Dissipation ⁴	100	W
T _{STG}	Storage Temperature Range	-55 to 175	°C
T _J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹ (t≤10S)	---	20	°C/W
	Thermal Resistance Junction-ambient ¹ (Steady State)	---	50	°C/W
R _{θJC}	Thermal Resistance Junction-case ¹	---	3.6	°C/W

Table 3. Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

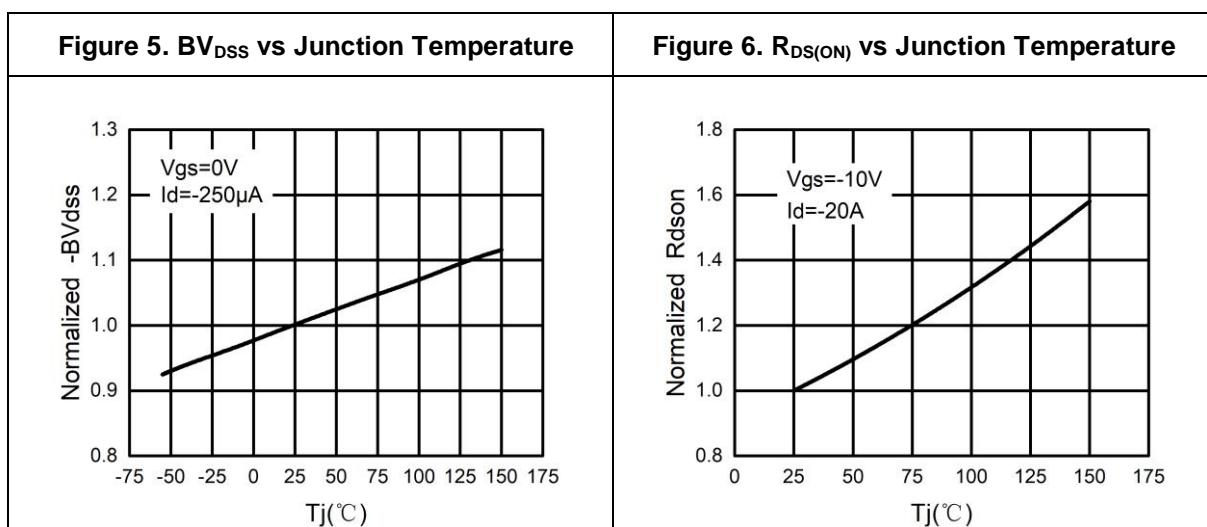
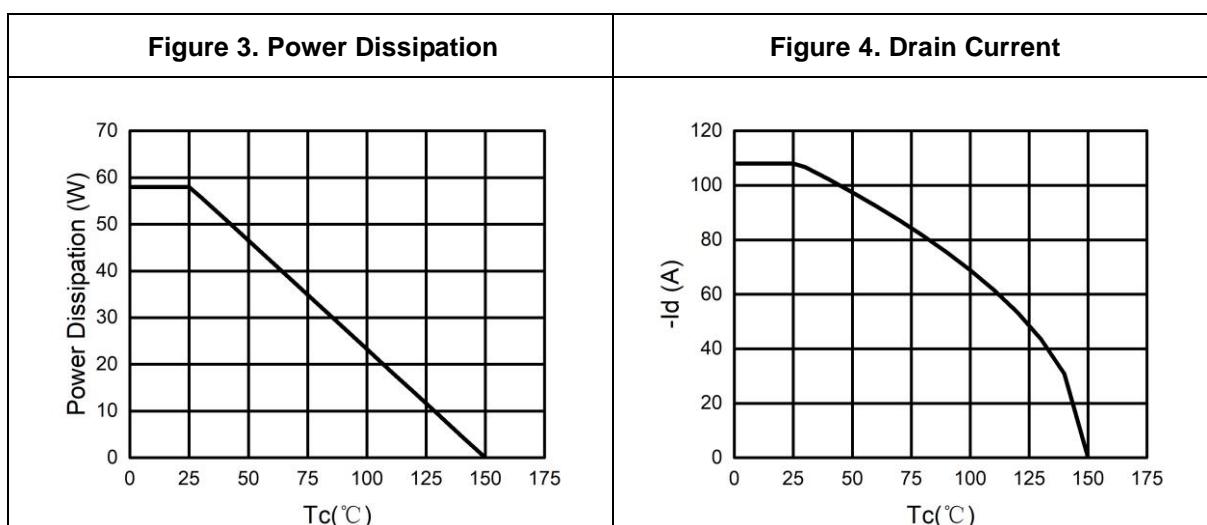
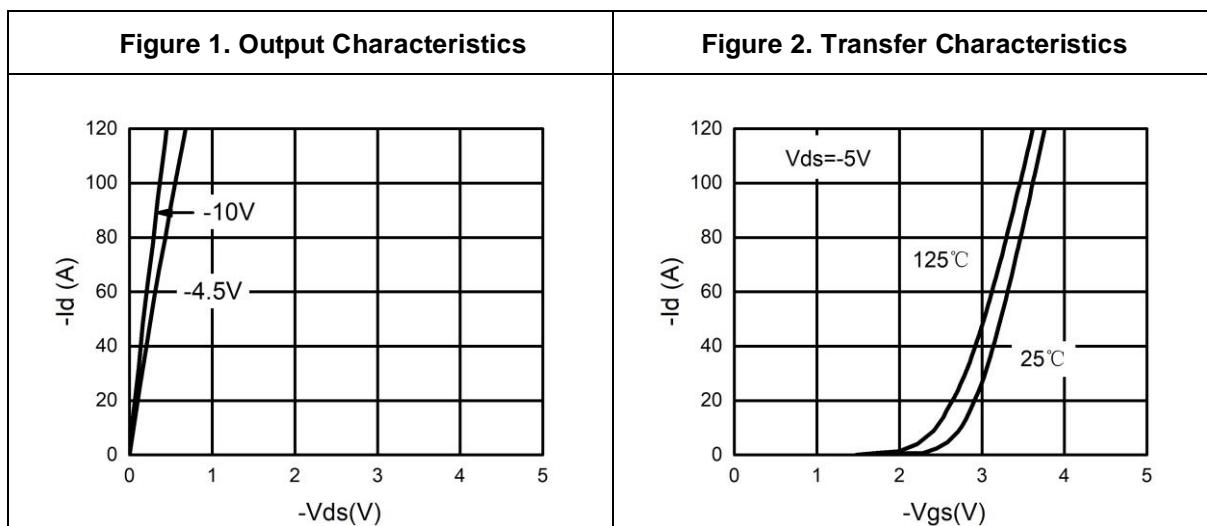
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{D}}=-250\mu\text{A}$	-30			V
$I_{\text{DS}(\text{S})}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-30\text{V}$, $V_{\text{GS}}=0\text{V}$			-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$			± 100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=-250\mu\text{A}$	-1	-1.7	-2.5	V
g_{FS}	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$, $I_{\text{D}}=-20\text{A}$		65		S
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-10\text{V}$, $I_{\text{D}}=-20\text{A}$		2.5	3.1	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_{\text{D}}=-20\text{A}$		4	5.2	$\text{m}\Omega$
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1.0\text{MHz}$		7000		pF
C_{oss}	Output Capacitance			820		pF
C_{rss}	Reverse Transfer Capacitance			540		pF
R_g	Gate resistance	$V_{\text{GS}}=0\text{V}$, $V_{\text{DS}}=0\text{V}$, $f=1.0\text{MHz}$		2.2		Ω
Switching Parameters						
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{GS}}=-10\text{V}$, $V_{\text{DS}}=-15\text{V}$, $R_L=0.75\Omega$, $R_{\text{GEN}}=3\Omega$		14		nS
t_r	Turn-on Rise Time			13		nS
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time			65		nS
t_f	Turn-Off Fall Time			37		nS
Q_g	Total Gate Charge	$V_{\text{GS}}=-10\text{V}$, $V_{\text{DS}}=-15\text{V}$, $I_{\text{D}}=-20\text{A}$		130		nC
Q_{gs}	Gate-Source Charge			12		nC
Q_{gd}	Gate-Drain Charge			31		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				-108	A
V_{SD}	Forward on Voltage (Note 3)	$V_{\text{GS}}=0\text{V}$, $I_{\text{S}}=-20\text{A}$			-1.2	V
t_{rr}	Reverse Recovery Time	$I_{\text{F}}=-20\text{A}$, $d\text{I}/dt=100\text{A}/\mu\text{s}$		30		ns
Q_{rr}	Reverse Recovery Charge	$I_{\text{F}}=-20\text{A}$, $d\text{I}/dt=100\text{A}/\mu\text{s}$		40		nC

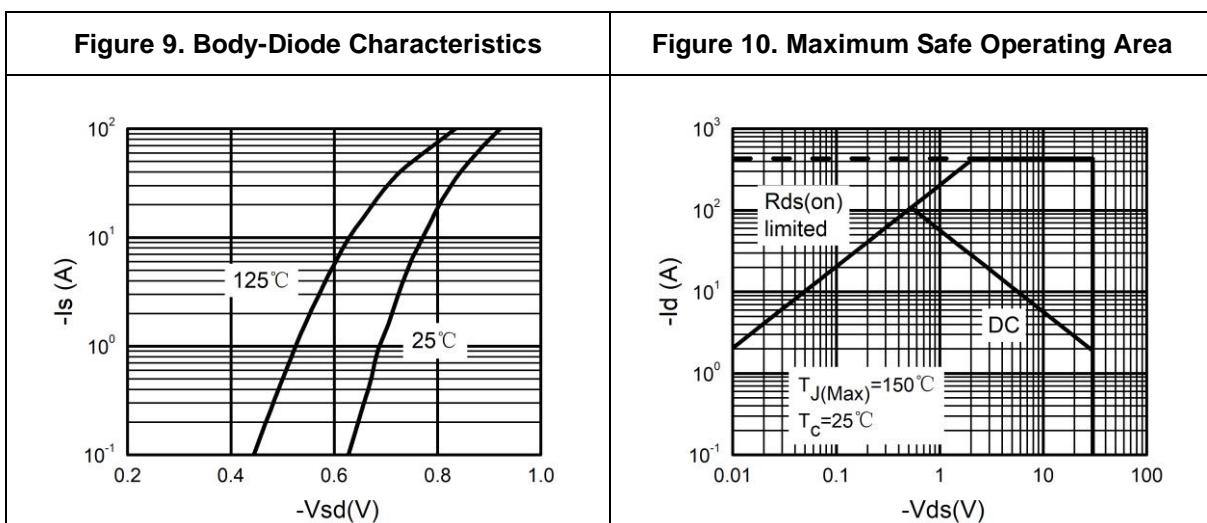
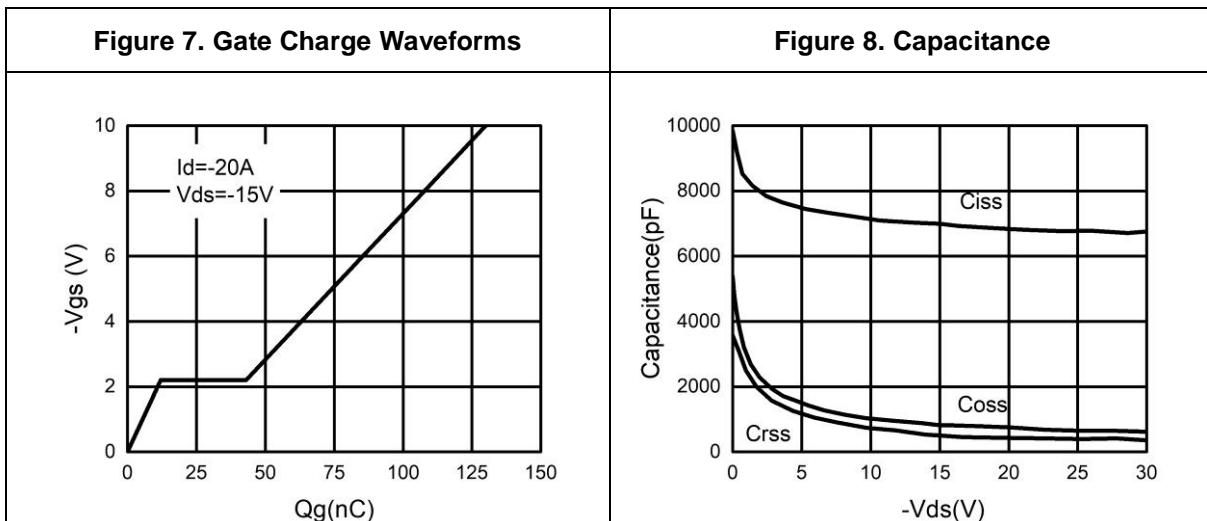
Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.EAS condition: $T_J=25^\circ\text{C}$, $V_{\text{DD}}=15\text{V}$, $V_G=-10\text{V}$, $R_g=25\Omega$, $L=0.5\text{mH}$.

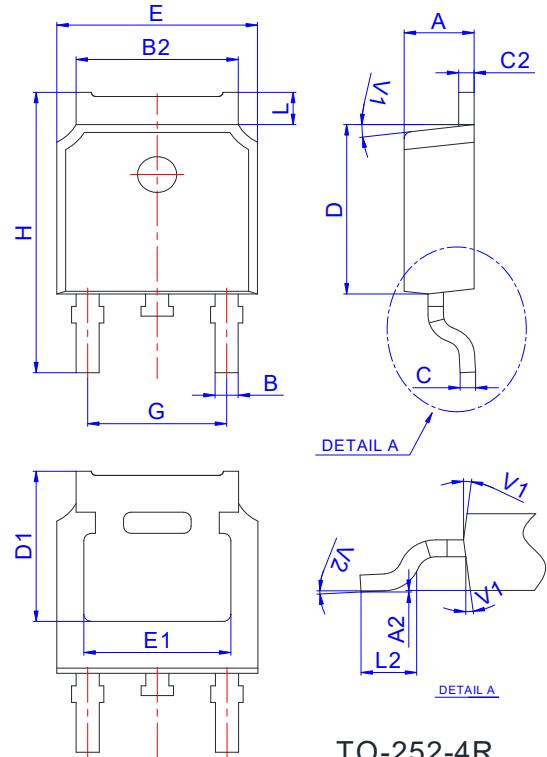
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)



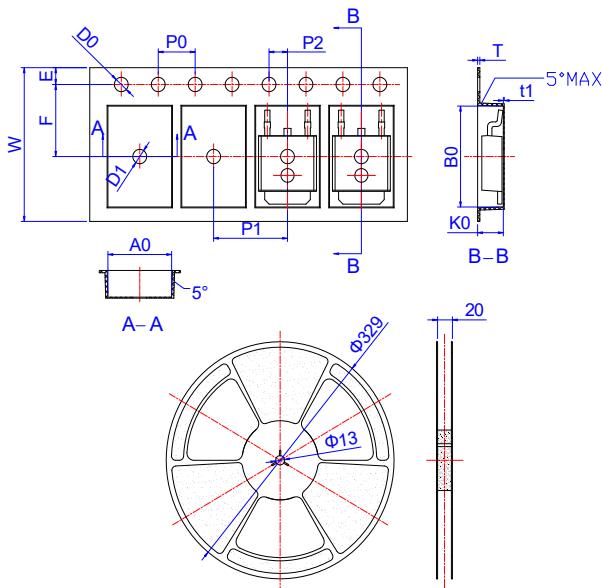


Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583